

IN THE CLAIMS:

Please amend the claims as follows.

1. (Original) A method for manufacturing a nitride semiconductor chip, said method comprising the steps of:

growing nitride crystals of a hexagonal system on a substrate surface; and
cutting said substrate along two directions that form a 120 degree angle.

2. (Original) A method according to claim 1, further comprising, between said growing step and said cutting step, the step of grinding the back surface of said substrate.

3. (Original) A method according to claim 2, further comprising the step of:

making scratches on the front or back surface of said substrate, between said grinding step and said cutting step, wherein
said cutting step is performed by cutting said substrate along the directions of said scratches.

4. (Original) A method according to claim 1, wherein said semiconductor chip has a planer shape of a rhombus.

5. (Original) A method according to claim 1, wherein said substrate is sapphire.

6. (Original) A method according to claim 1, wherein said nitride crystals include GaN.

7. (Original) A nitride semiconductor chip, comprising:
 - a substrate; and
 - nitride crystals of a hexagonal system and formed on said substrate; wherein the planer shape of said semiconductor chip is a rhombus having an interior angle of 120 degrees.
8. (Original) A semiconductor chip according to claim 7, further comprising:
 - a light emitting section formed on the central section of said rhombus of the planer shape of said semiconductor chip; and
 - electrode sections formed at both ends of said rhombus to pinch said light emitting section.
9. (Original) A semiconductor chip according to claim 8, wherein the planer shape of said electrode sections is triangular.
10. (Presently Amended) A semiconductor chip according to claim 7, wherein said substrate is a sapphire.
11. (Presently Amended) A semiconductor chip according to claim 7, wherein said nitride crystals include a GaN.